

PTO/SB/08A (08-03)

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## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

**(Use as many sheets as necessary)**

**Complete if Known**

Application Number	10/618049
Filing Date	Jul 11, 2003
First Named Inventor	Mardilovich et al
Art Unit	
Examiner Name	
Attorney Docket Number	200300109-1

Sheet 1 of 1

## U. S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>2</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
		EP0346954	12-20-1989	Biginelli		
		EP0616053	09-21-1994	Atotech USA		
		WO 02/099162	12-12-2002	Qinetiq Limited		
		WO 03/049515	06-12-2003	Qinetiq Limited		
		WO 97/22733	06-26-1997	FST Intl		

**Examiner  
Signature**

Date Considered

3/9/06

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. \*Applicant's unique citation designation number (optional). \*See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. \*Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). \*For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. \*Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. \*Applicant is to place a check mark here if English language Translation is attached.

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**PATENT APPLICATION**

Sheet 1 of 1

<b>FORM PTO-1449</b>  <b>LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT</b>  (Use several sheets if necessary)	ATTY. DOCKET NO.	APPLICATION NO.	CONFIRMATION NO.
	200300109-1		
	APPLICANT		
	Peter Mardil vich et al.		
	FILING DATE	GROUP	

**REFERENCE DESIGNATION**

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	PUBLICATION DATE	NAME	Pages, Columns, Lines Where Relevant Passages or Figures Appear
HEA	1A	4,486,274	12/04/1984	Alys et al.	
HEA	1B	4,668,533	05/26/1987	Miller	
HEA	1C	5,882,736	03/16/1999	Stein et al.	
HEA	1D	5,980,998	11/09/1999	Sharma et al.	
HEA	1E	6,194,032	02/27/2001	Svedberg et al.	
HEA	1F	6,221,140	04/24/2001	Kobayashi et al.	
HEA	1G	6,402,403	06/11/2002	Speakman	
HEA	1H	6,563,057	05/13/2003	Hotta et al.	
HEA	1I	2001/0012869	08/09/2001	Fukushima et al.	
HEA	1J				
HEA	1K				

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	Pages/Columns/Lines Where Relevant Passages/Figures Appear	Check if Translation attached
	1L					
	1M					
	1N					
	1O					
	1P					

**OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)**

HEA	1Q	Mardilovich, Peter P., Ying She and Yi Hua Ma, "Defect-Free Palladium Membranes on Porous Stainless-Steel Support," AIChE JOURNAL, Vol. 44, No. 2, pp. 310-322, Feb. 1998.
HEA	1R	Kim, Changman, Yasushi Oikawa, Jaesoo Shin and Hajime Ozaki, "Ni Dot Array Formation on Scratches of Si(111) by Electroless Deposition," JPN. J. APPL. PHYS. Vol. 41, Part 2, No. 28, pp. L178-L179, Feb. 2002.
HEA	1S	Petrov, N., Y. Sverdlov, and Y. Shacham-Diamand, "Electrochemical Study of the Electroless Deposition of Co(P) and Co(W, P) Alloys," JOURNAL OF THE ELECTROCHEMICAL SOCIETY, 149 (4) C187-C194 (2002)

EXAMINER

DATE CONSIDERED